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672811  
Docket No. 0819-0425

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Haruko INOUE et al. ) Group Art Unit: 2811  
Serial No. 09/666,156 ) Examiner: S. Loke  
Filed: September 19, 2000 )  
For: HIGH-VOLTAGE MOS )  
TRANSISTOR AND METHOD )  
FOR FABRICATING THE SAME )

#5  
4/16/02  
VLS

CERTIFICATE OF MAILING

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*[Signature]*

RESPONSE TO ELECTION REQUIREMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the election requirement in the Office Action of February 20, 2002,  
Applicants hereby elect without traverse the Group I claims - that is, claims 1-7, drawn to a  
semiconductor device.

Examination on the merits is requested.

Respectfully submitted,

*[Signature]*  
Eric J. Robinson  
Registration No. 38,285

NIXON PEABODY LLP  
8180 Greensboro Drive, Suite 800  
McLean, Virginia 22102  
(703) 790-9110

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